

<b>L Numb r</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
1	18	5665260, 2002/0027130	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:16
2	8	(5665260, 2002/0027130) and Ca	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:17
4	4	((5665260, 2002/0027130) and Ca) and ppm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:18
3	1	((5665260, 2002/0027130) and Ca) and weight	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:57
5	0	((5665260, 2002/0027130) and Ca) and ppm) and Na	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:36
6	4	((5665260, 2002/0027130) and Ca) and ppm) and B	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:25
7	35	6475606, 5753893, 5750958, "5721062"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:26
8	22	(6475606, 5753893, 5750958, "5721062") and weight	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:27
9	3	(6475606, 5753893, 5750958, "5721062") and weight with ppm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:40
10	0	((6475606, 5753893, 5750958, "5721062") and weight) and weight with percntage	USPAT; US-PGPUB; EP ; JP ; DERWENT; IBM_TDB	2003/08/05 13:32

11	0	((6475606, 5753893, 5750958, "5721062") and weight) and weight with percentage	USPAT; US-PUB; EP; JPO; DERWENT; IBM_TDB	2003/08/05 13:40
12	3	((6475606, 5753893, 5750958, "5721062") and weight) and weight with percent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:33
13	4	((6475606, 5753893, 5750958, "5721062") and weight) and Na	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:36
14	98	ceramic adj heater and Na	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:18
15	17	(ceramic adj heater and Na) and weight with ppm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:40
16	15	(ceramic adj heater and Na) and weight with percentage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:41
17	6	((ceramic adj heater and Na) and weight with ppm) and ((ceramic adj heater and Na) and weight with percentage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:45
18	2	(ceramic adj heater and Na) and Na with percentage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:49
19	0	(ceramic adj heater and Na) and y with percentage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:48
20	13	(ceramic adj heater and Na) and Na with ppm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:12

21	0	(6475606, 5753893, 5750958, "5721062") and Li with weight	USPAT; US-PGPUB; EP ; JP ; DERWENT; IBM_TDB	2003/08/05 13:58
22	0	(5665260, 2002/0027130) and Li with weight	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 13:58
23	3	(6475606, 5753893, 5750958, "5721062") and Ca with weight	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:03
24	4	(ceramic adj heater and Na) and Ca with weight	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:08
25	2	(5665260, 2002/0027130) and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:15
26	10	(6475606, 5753893, 5750958, "5721062") and nitride adj ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:15
27	313501	ceramic adj heater same semiconductor wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:32
28	1	(ceramic adj heater same semiconductor wafer) and distance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:20
29	57870	(ceramic adj heater same semiconductor wafer) and distance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:21
30	4339	((ceramic adj heater same semiconductor wafer) and distance) and distance same micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:22

31	2611	((c ramic adj heater sam s miconduct r wafer) and distance) and distance with micron	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:23
32	127	((c ramic adj heat r sam s mic nductor wafer) and distance) and distance with one adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:32
33	0	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and 219/444	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:27
34	0	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and ceramic adj substrate with thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:25
35	0	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and ceramic adj substrate with thermal adj conductivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:38
36	0	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and supporting adj pin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:26
37	2	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:28
38	2	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and 428/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:30
39	47	((((ceramic adj heater same semiconductor wafer) and distance) and distance with one adj micron) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:34
40	181	ceramic adj heater same semiconductor adj wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:32

41	0	(c ramic adj h at r same s mic nductor adj wafer) and distance with n adj micr n	USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB	2003/08/05 15:30
42	0	(c ramic adj h ater sam s mic nductor adj wafer) and distance with ten adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:33
43	0	(ceramic adj heater same semiconductor adj wafer) and distance with fifty adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:35
44	181	(ceramic adj heater same semiconductor adj wafer) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:34
45	0	(ceramic adj heater same semiconductor adj wafer) and one adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:34
46	0	(ceramic adj heater same semiconductor adj wafer) and distance with micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:36
47	0	(ceramic adj heater same semiconductor adj wafer) and apart with micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:36
48	495	ceramic adj substrate with thermal adj conductivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:38
49	38	( ceramic adj substrate with thermal adj conductivity) and ceramic adj heater	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:38
50	172771	(( ceramic adj substrate with thermal adj conductivity) and ceramic adj heater) and ceramic substrate with thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:39

51	29	(( ceramic adj substrate with thermal adj c nductivity) and c ramic adj h at r) and c ramic adj substrate with thickn ss	USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB	2003/08/05 14:39
52	0	(c ramic adj heat r same semiconductor adj wafer) and distance same one adj micron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 15:31
54	9	(ceramic adj heater same semiconductor adj wafer) and distance same apart	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 15:31
53	47	(ceramic adj heater same semiconductor adj wafer) and distance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 15:50